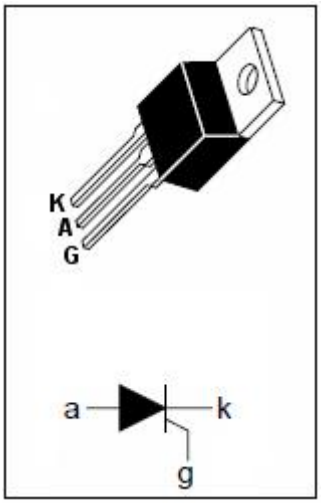
isc Thyristors TIC106N

APPLICATIONS

- 5A contimunous on-state current
- 30A surge-current
- Glass passivated
- Max I_{GT} of 200 μA
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	MIN	UNIT
V_{DRM}	Repetitive peak off-state voltage	800	V
V_{RRM}	Repetitive peak reverse voltage	800	V
$I_{T(AV)}$	On-state current Tc=80℃	3.2	A
$I_{T(RMS)}$	RMS on-state current Tc=80℃	5	A
I_{TM}	Surge peak on-state current	30	A
P_{GM}	Peak gate power P_W≤300 μs	1.3	W
$P_{G(AV)}$	Average gate power	0.3	W
T_j	Operating Junction temperature	110	℃
T_{stg}	Storage temperature	-40 ~+125	℃
$R_{th(j-c)}$	Thermal resistance, junction to case	1.9	℃/W
$R_{th(j-a)}$	Thermal resistance, junction to ambient	62.5	℃/W



ELECTRICAL CHARACTERISTICS (T_C=25℃ unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
I_{RRM}	Repetitive peak reverse current	V_{RM}=V_{RRM}, V_{RM}=V_{RRM}, Tj=110℃			0.4 1.0	mA
I_{DRM}	Repetitive peak off-state current	V_{DM}=V_{DRM}, V_{DM}=V_{DRM}, Tj=110℃			0.4 1.0	mA
V_{TM}	On-state voltage	I_{TM}= 5A			1.7	V
I_{GT}	Gate-trigger current	V_{AA}=6V; R_L=1kΩ			200	μA
V_{GT}	Gate-trigger voltage	V_{AA}=6V; R_L=100Ω			1.0	V
I_H	Holding current	V_{AA}=6V; R_{GK}=1kΩ, I_T= 10mA			5	mA

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